

# 1200V SiC Schottky Diode

## Amp+<sup>™</sup> Features

- Unipolar rectifier with surge current
- Zero reverse recovery current
- · Fast, temperature-independent switching
- Avalanche tested to 200mJ\*
- All parts tested to greater than 1,400V

## Amp+<sup>™</sup> Benefits

- Near zero switching loss
- Higher efficiency
- Smaller heat sink
- Easy to parallel

## Amp+<sup>™</sup> Applications

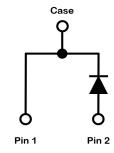
- Solar Inverters
- · Switch mode power supplies, UPS
- Power factor correction
- EV charging stations

# GP3D015A120B

VDC	1200 V
Q <sub>c</sub>	86 nC
I <sub>F</sub>	15 A
T <sub>j</sub> ,max	175 °C







Part #	Package	Marking
GP3D015A120B	TO-247-2L	3D015A120



#### Maximum Ratings, at Ti=25 °C, unless otherwise specified

Characteristics	Symbol	Conditions	Values	Unit	
		T <sub>C</sub> =25 °C, T <sub>j</sub> =175 °C	43		
Continuous forward current	I <sub>F**</sub>	T <sub>c</sub> =125 °C, T <sub>j</sub> =175 °C	23	A	
		T <sub>C</sub> =150 °C, T <sub>j</sub> =175 °C	15		
Surge non-repetitive forward current		T <sub>C</sub> =25 °C, t <sub>p</sub> =8.3 ms	150	•	
sine halfwave	I <sub>FSM</sub>	T <sub>C</sub> =110 °C, t <sub>p</sub> =8.3 ms	120	— A	
Non-repetitive peak forward current	I <sub>F,max</sub>	T <sub>C</sub> =25 °C, t <sub>p</sub> =10 μs	900	A	
<i>i<sup>2</sup>t</i> value	∫i²dt	T <sub>C</sub> =25 °C, t <sub>p</sub> =8.3 ms	93	^2	
		T <sub>C</sub> =110 °C, t <sub>p</sub> =8.3 ms	60	— A <sup>2</sup> s	
Repetitive peak reverse voltage	V <sub>RRM</sub>	T <sub>j</sub> =25 °C	1200	V	
Diode <i>dv/dt</i> ruggedness	dv/dt	Turn-on slew rate, repetitive	200	V/ns	
Power dissipation	P <sub>tot**</sub>	T <sub>c</sub> =25 °C	197	W	
Operating junction & storage temperature	T <sub>j</sub> , T <sub>storage</sub>	Continuous	-55175	°C	
Soldering temperature	T <sub>solder</sub>	Wave soldering leads	260	°C	
Mounting torque		M3 Screw	1	N-m	
Notes:		·			

Notes:

\* EAS of 200 mJ is based on starting Tj = 25°C, L = 1.0 mH, IAS = 20.00 A, V = 50 V.

\*\* Typical Rth<sub>JC</sub> used

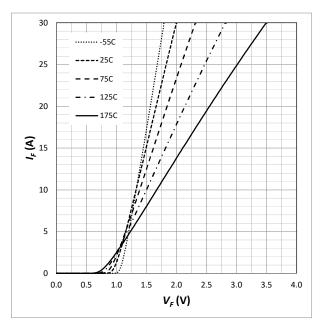
Characteristics	Symbol	Conditions	Values			Unit
	Symbol		min.	typ.	max.	
DC blocking voltage	V <sub>DC</sub>	T <sub>j</sub> =25 °C	1200	-	-	V
Breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> =1.00mA, T <sub>j</sub> =25 °C	1400	-	-	V
Diode forward voltage		I <sub>F</sub> =15A, T <sub>j</sub> =25 °C	-	1.48	1.60	
	V <sub>F</sub>	I <sub>F</sub> =15A, T <sub>j</sub> =125 °C	-	1.79	-	V
		I <sub>F</sub> =15A, T <sub>j</sub> =175 °C	-	2.10	2.70	
Reverse current	I <sub>R</sub>	V <sub>R</sub> =1,200V, T <sub>j</sub> =25 °C	-	1	30	μΑ
		V <sub>R</sub> =1,400V, T <sub>j</sub> =25 °C	-	6	-	
		V <sub>R</sub> =1,200V, T <sub>j</sub> =125 °C	-	10	-	
		V <sub>R</sub> =1,200V, T <sub>j</sub> =175 °C	-	41	450	
Total capacitive charge	Q <sub>c</sub>	V <sub>R</sub> =800V, T <sub>j</sub> =25 °C	-	86	-	nC
Total capacitance	с	V <sub>R</sub> =1V, f=1 MHz	-	962	-	pF
		V <sub>R</sub> =400V, f=1 MHz	-	81	-	
		V <sub>R</sub> =800V, f=1 MHz	-	59	-	

### Electrical Characteristics, at T<sub>j</sub>=25 °C, unless otherwise specified

#### **Thermal Characteristics**

Characteristics	Symbol	Conditions	Values			Unit
		Conditions	min.	typ.	max.	Onit
Thermal resistance, junction-case	$R_{thJC}$	-	-	0.76	0.93	°C/W

### **Typical Performance**





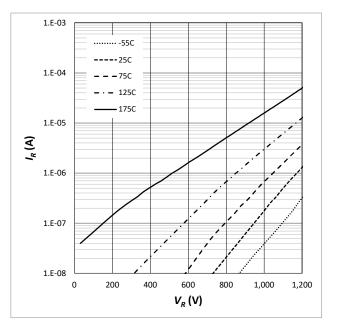


Fig. 2 Reverse Characteristics (parameterized on T<sub>i</sub>)

250

200

150

100

50

 $P_{Total}(W)$ 

125

175

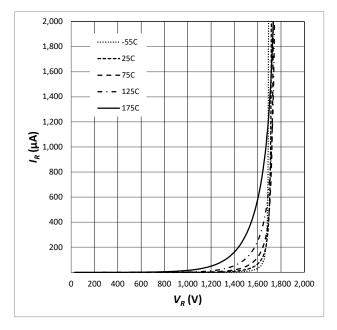
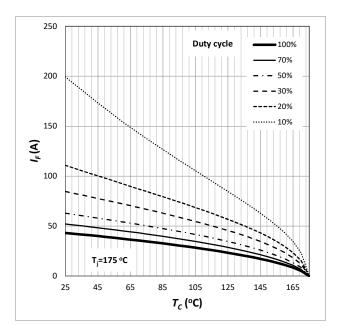


Fig. 3 Reverse Characteristics (parameterized on Tj)



T<sub>j</sub>=175 °C

Fig. 4 Power Derating



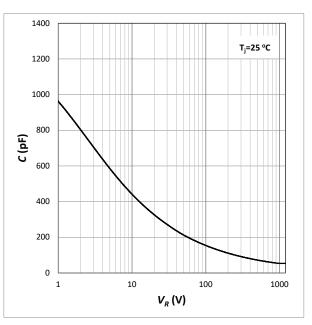
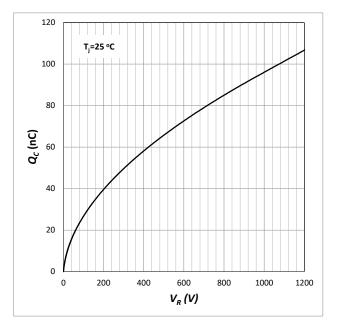


Fig. 5 Capacitance

Fig. 6 Capacitance

**1200V SiC Schottky Diode** 



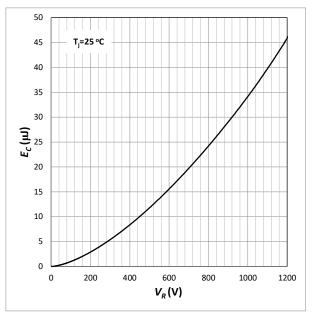


Fig. 7 Capacitive Charge

Fig. 8 Typical Capacitance Stored Energy

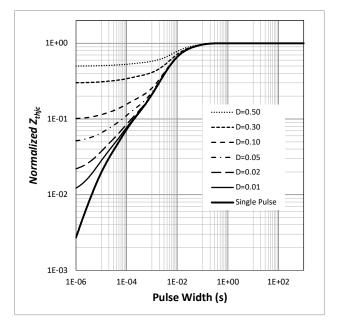


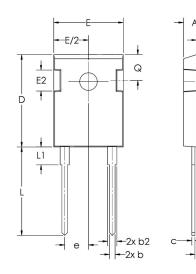
Fig. 9 Transient Thermal Impedance

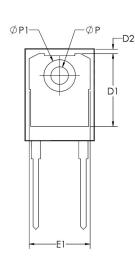
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# Amp+<sup>™</sup>

### GP3D015A120B

#### Package Dimensions TO-247-2L





Α2

A1

S

4

C) ma	Millin	neters	Inches		
Sym	Min	Max	Min	Max	
А	4.70	5.31	0.185	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b2	1.65	2.39	0.065	0.094	
С	0.38	0.89	0.015	0.035	
D	20.80	21.46	0.819	0.845	
D1	13.08	17.65	0.515	0.695	
D2	0.51	1.35	0.020	0.053	
E	15.49	16.26	0.610	0.640	
E1	13.46	14.16	0.530	0.557	
E2	3.43	5.49	0.135	0.216	
е	5.44 BSC		.214 BSC		
L	19.81	20.32	0.780	0.800	
L1	4.10	4.50	0.161	0.177	
ØP	3.56	3.66	0.140	0.144	
ØP1	7.06	7.39	0.278	0.291	
Q	5.38	6.20	0.212	0.244	
s	6.04	6.30	0.238	0.248	

#### <u>Notes</u>

#### **RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

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